National Semiconductor

MM54C910/MM74C910 256 Bit TRI-STATE® Random Access Read/Write Memory

General Description

The MM54C910/MM74C910 is a 64 word by 4 bit random access memory. Inputs consist of six address lines, four data input lines, a $\overline{WE}$, and a $\overline{ME}$ line. The six address lines are internally decoded to select one of 64 word locations. An internal address register latches the address information on the positive to negative transition of $\overline{ME}$. The TRI-STATE outputs allow for easy memory expansion.

Address Operation: Address inputs must be stable (t_{SA}) prior to the positive to negative transition of $\overline{ME}$, and (t_{HA}) after the positive to negative transition of $\overline{ME}$. The address register holds the information and stable address inputs are not needed at any other time.

Write Operation: Data is written into memory at the selected address if $\overline{WE}$ goes low while $\overline{ME}$ is low. $\overline{WE}$ must be held low for $t_{\overline{WE}}$ and data must remain stable t_{HD} after $\overline{WE}$ returns high.

Read Operation: Data is nondestructively read from a memory location by an address operation with $\overline{WE}$ held high.

Outputs are in the TRI-STATE (Hi-Z) condition when the device is writing or disabled.

Features

■ Supply voltage range	3.0 V to 5.5 V
■ High noise immunity	0.45 V_{CC} (typ.)
■ TTL compatible fan out	1 TTL load
■ Input address register	
■ Low power consumption	250 nW/package (typ.) (chip enabled or disabled)
■ Fast access time	250 ns (typ.) at 5.0 V
■ TRI-STATE outputs	
■ High voltage inputs	

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See page 4-11 for Detailed Specifications